



NTE5688, NTE5689, NTE5690 TRIAC - 40Amp, 1/2" Press Fit

Absolute Maximum Ratings:

Repetitive Peak Off-State Voltage (Gate Open, $T_J = +110^\circ\text{C}$, Note 1), V_{DRM}

NTE5688	200V
NTE5689	400V
NTE5690	600V

RMS On-State Current ($T_C = +80^\circ\text{C}$, Conduction Angle = 360°), $I_T(\text{RMS})$ 40A

Non-Repetitive Peak Surge On-State Current (One-Cycle, at 50Hz or 60Hz), I_{TSM} 400A

Peak Gate-Trigger Current (for 3μs Max), I_{GTM} 12A

Peak Gate-Power Dissipation ($I_{\text{GT}} \leq I_{\text{GTM}}$), P_{GM} 40W

Average Gate-Power Dissipation, $P_{\text{G(AV)}}$ 750mW

Operating Temperature Range, T_{opr} -40° to +110°C

Storage Temperature Range, T_{stg} -40° to +150°C

Thermal Resistance, Junction-to-Case, R_{thJC} 1.8°C/W Typ

Electrical Characteristics: (At Specified Case Temperature)

Peak Off-State Current, I_{DRM} (Gate Open, $T_C = +110^\circ\text{C}$, $V_{\text{DRM}} = \text{Max Rating}$, Note 1) 1mA Max

Maximum On-State Voltage ($T_C = +25^\circ\text{C}$, $I_T = 40\text{A}$, Note 1), V_{TM} 2.0V Max

DC Holding Current (Gate Open, $T_C = +25^\circ\text{C}$, Note 1), I_{Hold} 60mA Max

Critical Rate-of-Rise of Off-State Voltage, Critical dv/dt ($V_D = V_{\text{DRM}}$, Gate Open, $T_C = +110^\circ\text{C}$, Note 1) 200V/μs

Critical rate-of-Rise of commutation Voltage, Commutating dv/dt ($V_D = V_{\text{DRM}}$, $I_T = 40\text{A}$, Gate Unenergized, $T_C = +80^\circ\text{C}$, Note 1) 3V/μs

DC Gate-Trigger Current ($V_D = 12\text{VDC}$, $R_L = 30\Omega$, $T_C = +25^\circ\text{C}$), I_{GT} (T_{2+} Gate +, T_{2-} Gate -) Quads I and III 100mA Max

(T_{2+} Gate -, T_{2-} Gate +) Quads II and IV 150mA Max

DC Gate-Trigger Voltage ($V_D = 12\text{VDC}$, $R_L = 30\Omega$, $T_C = +25^\circ\text{C}$), V_{GT} 2.5V Max

Gate-Controlled Turn-On Time, T_{gt} ($V_D = 400\text{V}$, $I_{\text{GT}} = 200\text{mA}$, $t_R = 0.1\mu\text{s}$, $I_T = 10\text{A}$ (Peak), $T_C = +25^\circ\text{C}$) 3μs

Note 1. All values apply in either direction.

